

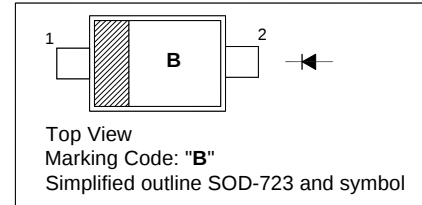
RB521G-30G

Silicon Epitaxial Planar Schottky Barrier Diode

for rectifying small power application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



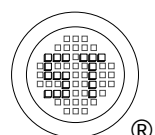
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

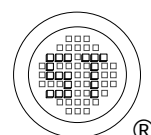
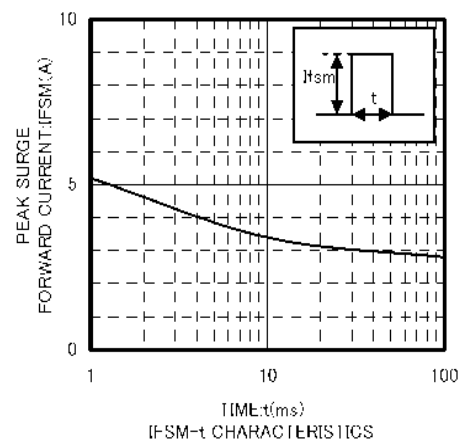
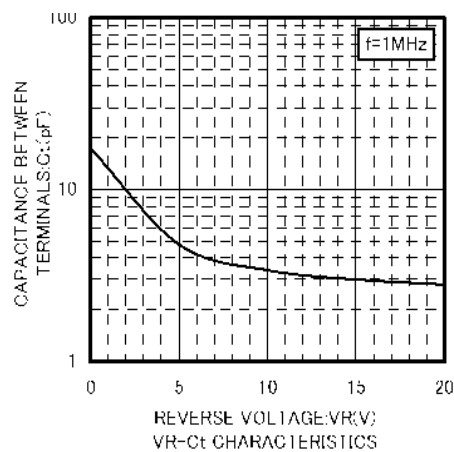
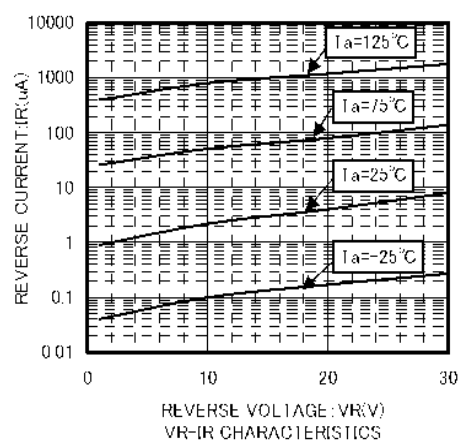
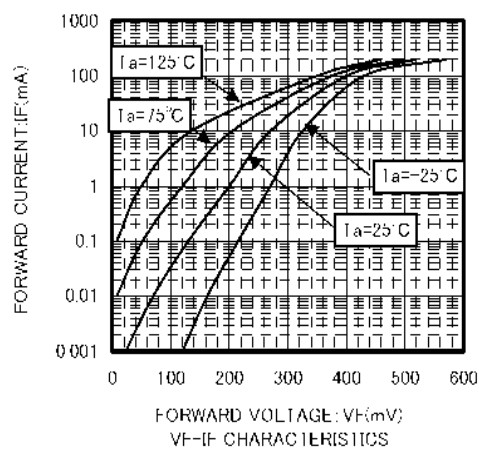
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Forward Rectified Current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.35	V
Reverse Current at $V_R = 10\text{ V}$	I_R	10	μA

Note: Please pay attention to static electricity when handling.





PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-723

